NL27WZ17

Dual Non-Inverting Schmitt Trigger Buffer

The NL27WZ17 is a high performance dual buffer operating from a 1.65 to 5.5 V supply. At V_{CC} = 3.0 V, high impedance TTL compatible inputs significantly reduce current loading to input drivers while the TTL compatible outputs offer improved switching noise performance.

Features

- Extremely High Speed: t_{PD} 2.0 ns (typical) at V_{CC} = 5.0 V
- Designed for 1.65 V to 5.5 V V_{CC} Operation
- Overvoltage Tolerant Inputs
- LVTTL Compatible − Interface Capability with 5.0 V TTL Logic with V_{CC} = 3.0 V (2.7–3.3)
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability at V_{CC} = 3.0 V
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Chip Complexity: FET = 72; Equivalent Gate = 18
- Pb−Free Package is Available

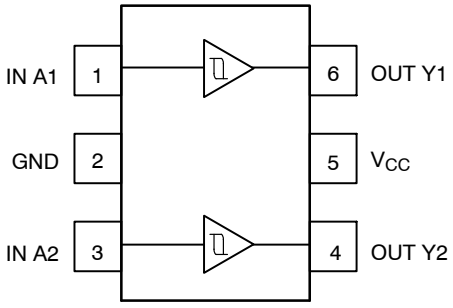

Figure 1. Pinout (Top View)

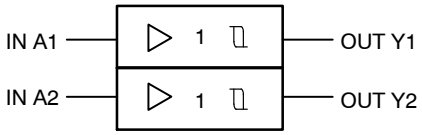

Figure 2. Logic Symbol

PIN ASSIGNMENT

1	IN A1
2	GND
3	IN A2
4	OUT Y2
5	V_{CC}
6	OUT Y1

FUNCTION TABLE

A Input	$\overline{Y}$ Output
L	L
H	H

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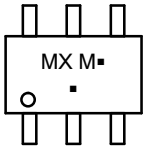
SC−88/SOT−363/SC−70
DF SUFFIX
CASE 419B

MARKING DIAGRAM



Pin 1

MX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NL27WZ17DFT2	SC−88	3000/Tape & Reel
NL27WZ17DFT2G	SC−88 (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_I	DC Input Voltage		$-0.5 \le V_I \le +7.0$	V
V_O	DC Output Voltage	Output in Z or LOW State (Note 1)	$-0.5 \le V_O \le 7.0$	V
I_{IK}	DC Input Diode Current	V_I < GND	−50	mA
I_{OK}	DC Output Diode Current	V_O < GND	−50	mA
I_O	DC Output Sink Current		±50	mA
I_{CC}	DC Supply Current per Supply Pin		±100	mA
I_{GND}	DC Ground Current per Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
P_D	Power Dissipation in Still Air		200	mW
θ_{JA}	Thermal Resistance		333	°C/W
T_L	Lead Temperature, 1 mm from case for 10 s		260	°C
T_J	Junction Temperature under Bias		+150	°C
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 150 N/A	V
$I_{Latch-Up}$	Latch−Up Performance	Above V_{CC} and Below GND at 85°C (Note 5)	±500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. I_O absolute maximum rating must be observed.
2. Tested to EIA/JESD22−A114−A
3. Tested to EIA/JESD22−A115−A
4. Tested to JESD22−C101−A
5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Supply Voltage	Operating Data Retention Only	1.65 1.5	5.5 5.5	V
V_I	Input Voltage		0	5.5	V
V_O	Output Voltage	(High or LOW State)	0	5.5	V
T_A	Operating Free−Air Temperature		−55	+125	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate	V_{CC} = 2.5 V ±0.2 V V_{CC} = 3.0 V ±0.3 V V_{CC} = 5.0 V ±0.5 V	0 0 0	No Limit No Limit No Limit	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			−55°C ≤ T_A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	
V_T+	Positive Input Threshold Voltage		1.65 2.3 2.7 3.0 4.5 5.5	0.6 1.0 1.2 1.3 1.9 2.2	1.0 1.5 1.7 1.9 2.7 3.3	1.4 1.8 2.0 2.2 3.1 3.6	0.6 1.0 1.2 1.3 1.9 2.2	1.4 1.8 2.0 2.2 3.1 3.6	V
V_T-	Negative Input Threshold Voltage		1.65 2.3 2.7 3.0 4.5 5.5	0.2 0.4 0.5 0.6 1.0 1.2	0.5 0.75 0.87 1.0 1.5 1.9	0.8 1.15 1.4 1.5 2.0 2.3	0.2 0.4 0.5 0.6 1.0 1.2	0.8 1.15 1.4 1.5 2.0 2.3	V
V_H	Input Hysteresis Voltage		1.65 2.3 2.7 3.0 4.5 5.5	0.1 0.25 0.3 0.4 0.6 0.7	0.48 0.75 0.83 0.93 1.2 1.4	0.9 1.1 1.15 1.2 1.5 1.7	0.1 0.25 0.3 0.4 0.6 0.7	0.9 1.1 1.15 1.2 1.5 1.7	V
V_{OH}	High−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	I_{OH} = −100 μA I_{OH} = −3.0 mA I_{OH} = −8.0 mA I_{OH} = −12 mA I_{OH} = −16 mA I_{OH} = −24 mA I_{OH} = −32 mA	1.65−5.5 1.65 2.3 2.7 3.0 3.0 4.5	V_{CC} −0.1 1.29 1.9 2.2 2.4 2.3 3.8	V_{CC} 1.52 2.1 2.4 2.7 2.5 4.0		V_{CC} −0.1 1.29 1.9 2.2 2.4 2.3 3.8		V
V_{OL}	Low−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA I_{OL} = 4.0 mA I_{OL} = 8.0 mA I_{OL} = 12 mA I_{OL} = 16 mA I_{OL} = 24 mA I_{OL} = 32 mA	1.65−5.5 1.65 2.3 2.7 3.0 3.0 4.5		0.08 0.2 0.22 0.28 0.38 0.42	0.1 0.24 0.3 0.4 0.4 0.55 0.55		0.1 0.24 0.3 0.4 0.4 0.55 0.55	V
I_{IN}	Input Leakage Current	V_{IN} = V_{CC} or GND	0 to 5.5			±0.1		±1.0	μA
I_{OFF}	Power Off−Output Leakage Current	V_{OUT} = 5.5 V	0			1.0		10	μA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND	5.5			1.0		10	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			−55°C ≤ T_A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	
t_{PLH} t_{PHL}	Propagation Delay Input A to Y	R_L = 1.0 MΩ, C_L = 15 pF	1.65 1.8 2.5 ± 0.2 3.3 ± 0.3 5.0 ± 0.5	2.0 2.0 1.0 1.0 0.5	9.1 7.6 5.0 3.7 3.1	15 12.5 9.0 6.3 5.2	2.0 2.0 1.0 1.0 0.5	15.6 13 9.5 6.5 5.5	ns
		R_L = 500 Ω, C_L = 50 pF	3.3 ± 0.3 5.0 ± 0.5	1.5 0.8	4.4 3.7	7.2 5.9	1.5 0.8	7.5 6.2	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C_{IN}	Input Capacitance	V_{CC} = 5.5 V, V_I = 0 V or V_{CC}	7.0	pF
C_{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_I = 0 V or V_{CC} 10 MHz, V_{CC} = 5.5 V, V_I = 0 V or V_{CC}	9.0 11	pF

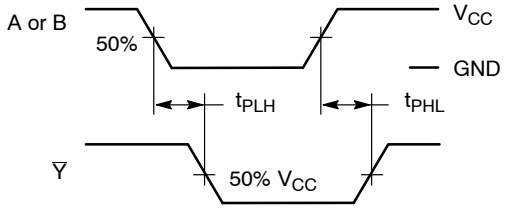
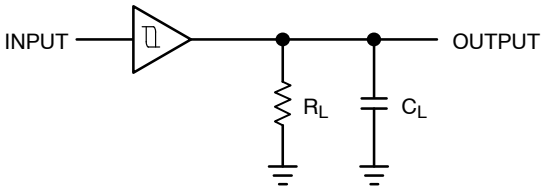


Figure 3. Switching Waveforms



A 1−MHz square input wave is recommended for propagation delay tests.

Figure 4. Test Circuit

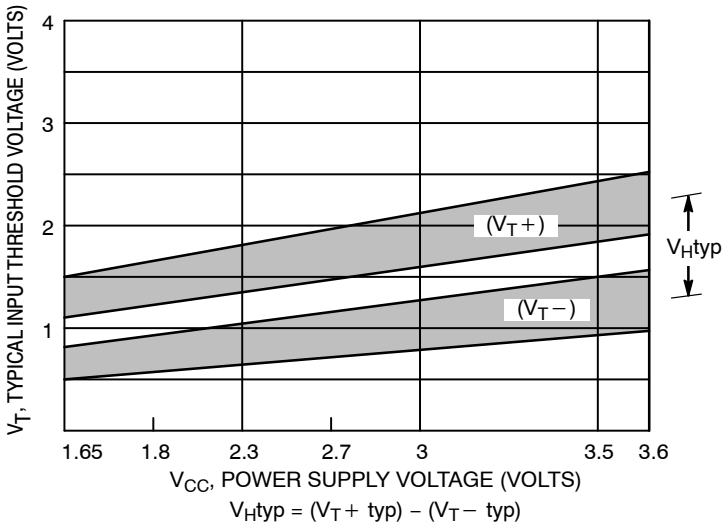
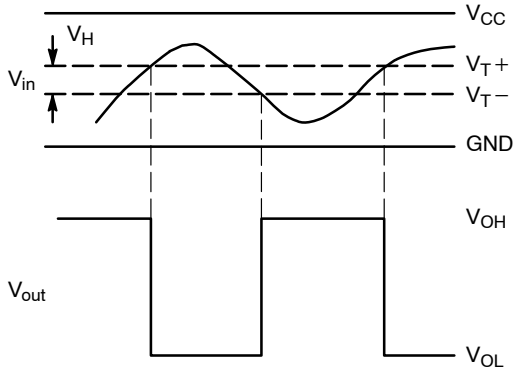
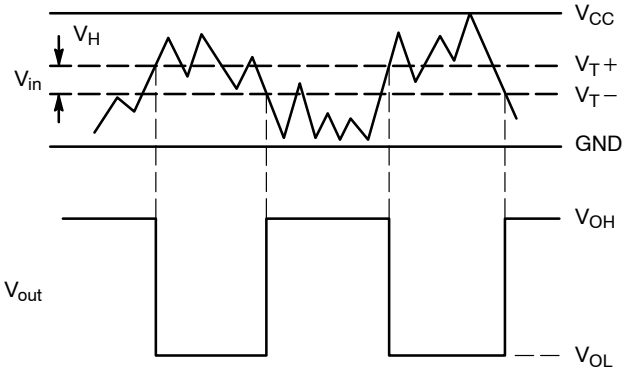


Figure 5. Typical Input Threshold, V_T+, V_T- versus Power Supply Voltage



(a) A Schmitt−Trigger Squares Up Inputs With Slow Rise and Fall Times

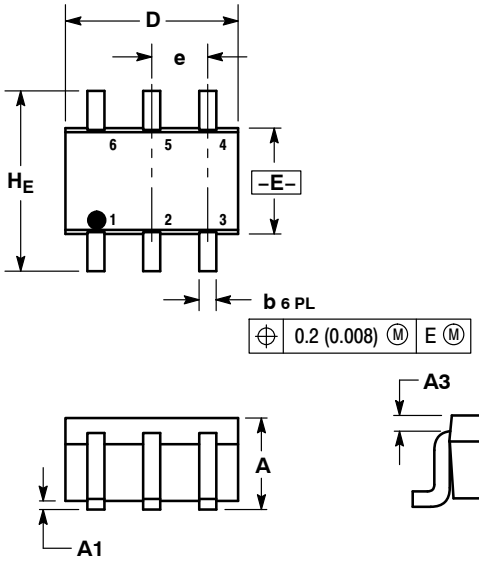


(b) A Schmitt−Trigger Offers Maximum Noise Immunity

Figure 6. Typical Schmitt−Trigger Applications

PACKAGE DIMENSIONS

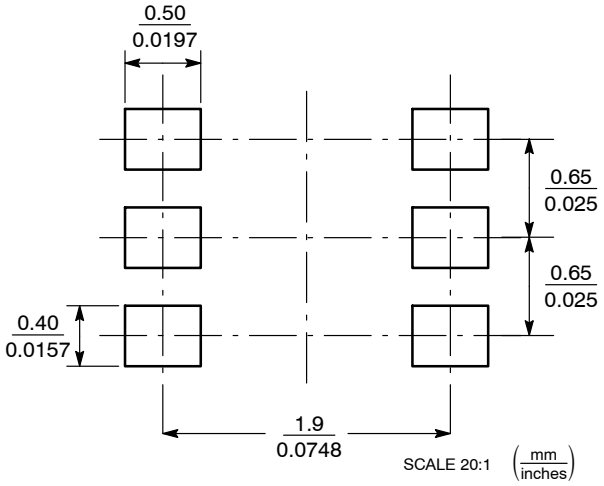
SC−88/SOT−363/SC70−6
DF SUFFIX
CASE 419B−02
ISSUE W



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B−01 OBSOLETE, NEW STANDARD 419B−02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3		0.20 REF			0.008 REF	
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e		0.65 BSC			0.026 BSC	
L	0.10	0.20	0.30	0.004	0.008	0.012
H_E	2.00	2.10	2.20	0.078	0.082	0.086

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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